Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

## 2SK2837

# Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain-source ON resistance :  $R_{DS (ON)} = 0.21 \Omega (typ.)$ 

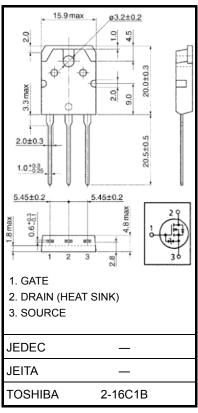
• High forward transfer admittance :  $|Y_{fs}| = 17 \text{ S (typ.)}$ 

• Low leakage current : I<sub>DSS</sub> = 100 μA (max) (V<sub>DS</sub> = 500 V)

Enhancement mode : V<sub>th</sub> = 2.0 to 4.0 V (V<sub>DS</sub> = 10 V, I<sub>D</sub> = 1 mA)

### **Absolute Maximum Ratings (Ta = 25°C)**

| Characteri                             | stics                  | Symbol           | Rating     | Unit |  |
|--|------------------------|------------------|------------|------|--|
| Drain-source voltage                   |                        | $V_{DSS}$        | 500        | V    |  |
| Drain-gate voltage (R                  | <sub>GS</sub> = 20 kΩ) | $V_{DGR}$        | 500        | V    |  |
| Gate-source voltage                    |                        | $V_{GSS}$        | ±30        | V    |  |
| Drain current                          | DC (Note 1)            | I <sub>D</sub>   | 20         | Α    |  |
|  | Pulse (Note 1)         | I <sub>DP</sub>  | 80         | Α    |  |
| Drain power dissipatio                 | n (Tc = 25°C)          | P <sub>D</sub>   | 150        | W    |  |
| Single pulse avalanche energy (Note 2) |                        | E <sub>AS</sub>  | 960        | mJ   |  |
| Avalanche current                      |                        | I <sub>AR</sub>  | 20         | Α    |  |
| Repetitive avalanche                   | energy (Note 3)        | E <sub>AR</sub>  | 15         | mJ   |  |
| Channel temperature                    |                        | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature r                  | ange                   | T <sub>stg</sub> | -55 to 150 | °C   |  |



Weight: 4.6 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

| Characteristics                        | Symbol                 | Max   | Unit |  |
|--|------------------------|-------|------|--|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 0.833 | °C/W |  |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 50    | °C/W |  |

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 4.08 mH,  $R_{G}$  = 25  $\Omega$ ,  $I_{AR}$  = 20 A

Note 3: Repetitive rating: Pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device.

Please handle with caution.



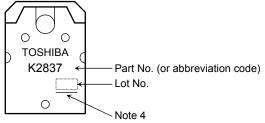
## **Electrical Characteristics (Ta = 25°C)**

| Charac  | cteristics      | Symbol               | Test Condition  | Min | Тур. | Max  | Unit |
|---|-----------------|----------------------|---|-----|------|------|------|
| Gate leakage cu                                 | irrent          | I <sub>GSS</sub>     | V <sub>GS</sub> = ±25 V, V <sub>DS</sub> = 0 V                        |     | _    | ±10  | μΑ   |
| Gate-source bre                                 | eakdown voltage | V (BR) GSS           | I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V                        | ±30 | _    | _    | V    |
| Drain cut-off cu                                | rrent           | I <sub>DSS</sub>     | V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V                        | _   | _    | 100  | μΑ   |
| Drain-source br                                 | eakdown voltage | V (BR) DSS           | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V                         | 500 | _    | _    | V    |
| Gate threshold v                                | oltage          | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA                         | 2.0 | _    | 4.0  | V    |
| Drain-source O                                  | N resistance    | R <sub>DS</sub> (ON) | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                         | _   | 0.21 | 0.27 | Ω    |
| Forward transfer                                | r admittance    | Y <sub>fs</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 10 A                         | 10  | 17   | _    | S    |
| Input capacitano                                | e               | C <sub>iss</sub>     |   |     | 3720 | _    | pF   |
| Reverse transfer capacitance                    |                 | C <sub>rss</sub>     | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz              | _   | 340  | _    |      |
| Output capacitance                              |                 | C <sub>oss</sub>     |   |     | 1165 | _    |      |
| Switching time                                  | Rise time       | t <sub>r</sub>       | $V_{\rm GS}$ $V_{\rm GS}$ $V_{\rm DD}$ $V_{\rm DD}$ $V_{\rm DD}$      | _   | 30   | _    | - ns |
|   | Turn-on time    | t <sub>on</sub>      |   | _   | 70   | _    |      |
|   | Fall time       | t <sub>f</sub>       |   | _   | 50   | _    |      |
|   | Turn-off time   | t <sub>off</sub>     | Duty $\leq 1\%$ , $t_{\mathbf{W}} = 10 \mu \text{s}$                  | _   | 290  | _    |      |
| Total gate charge (gate-source plus gate-drain) |                 | Qg                   | V <sub>DD</sub> ≈ 400 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6 A |     | 80   | 1    | nC   |
| Gate-source charge                              |                 | Q <sub>gs</sub>      |   |     | 48   |      |      |
| Gate-drain ("miller") Charge                    |                 | Q <sub>gd</sub>      |   |     | 32   | _    |      |

#### Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | _   | _   | _    | 20   | Α    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | _   | _   | _    | 80   | Α    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 20 A, V <sub>GS</sub> = 0 V |     | 540  | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dl <sub>DR</sub> / dt = 100 A / μs            | 1   | 5.4  | _    | μC   |

## Marking

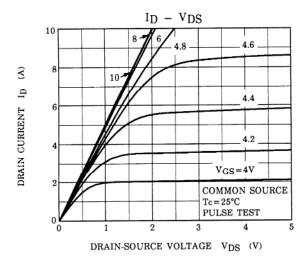


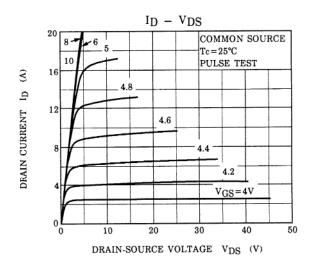
Note 4: A line under a Lot No. identifies the indication of product

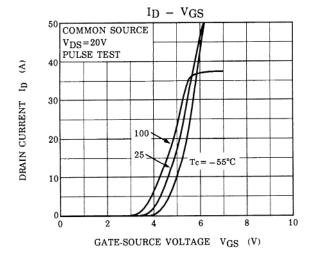
Not underlined: [[Pb]]/INCLUDES > MCV

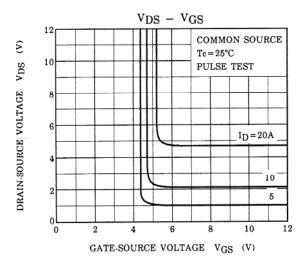
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

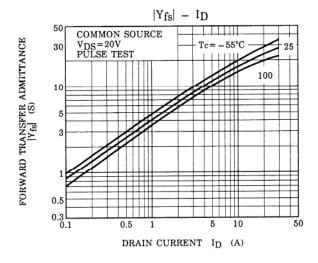
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

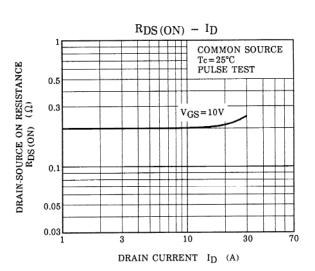




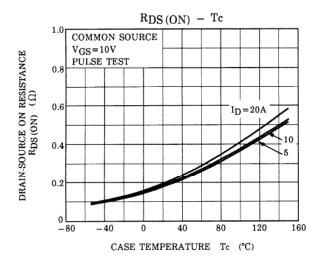


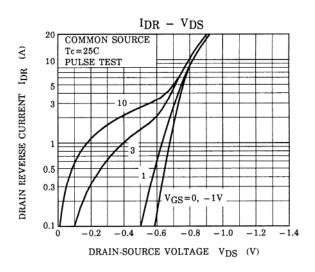


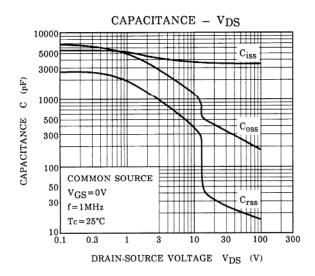


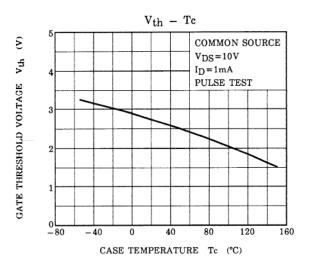


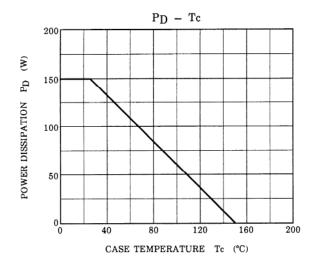
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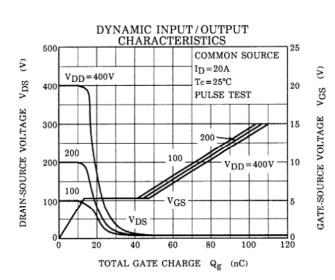




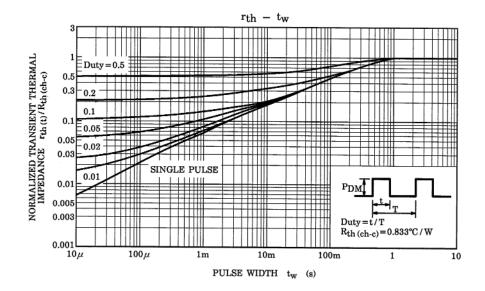


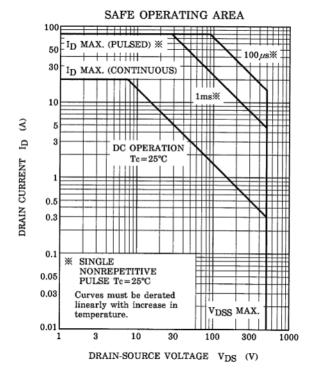


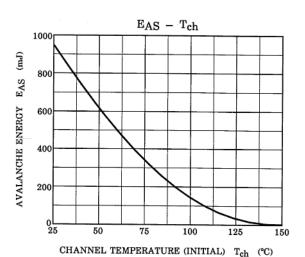


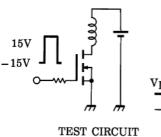


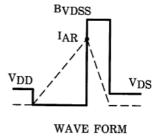
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$$R_G$$
 = 25  $\Omega$   
 $V_{DD}$  = 90 V, L = 4.08 mH

$$EAS = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left( \frac{BVDSS}{BVDSS - VDD} \right)$$

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